Renesas Electronics America Inc - R7FS124763A01CFM#AA0 Datasheet

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, I²C, SCI, SPI, UART/USART, USB
Peripherals	LVD, POR, PWM, WDT
Number of I/O	51
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 18x14b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs124763a01cfm-aa0

Table 1.11 Security

Feature	Functional description
AES	See section 38, AES Engine in User's Manual
True Random Number Generator (TRNG)	See section 39, True Random Number Generator (TRNG) in User's Manual

1.2 Block Diagram

Figure 1.1 shows the block diagram of the MCU superset. Individual devices within the group may have a subset of the features.

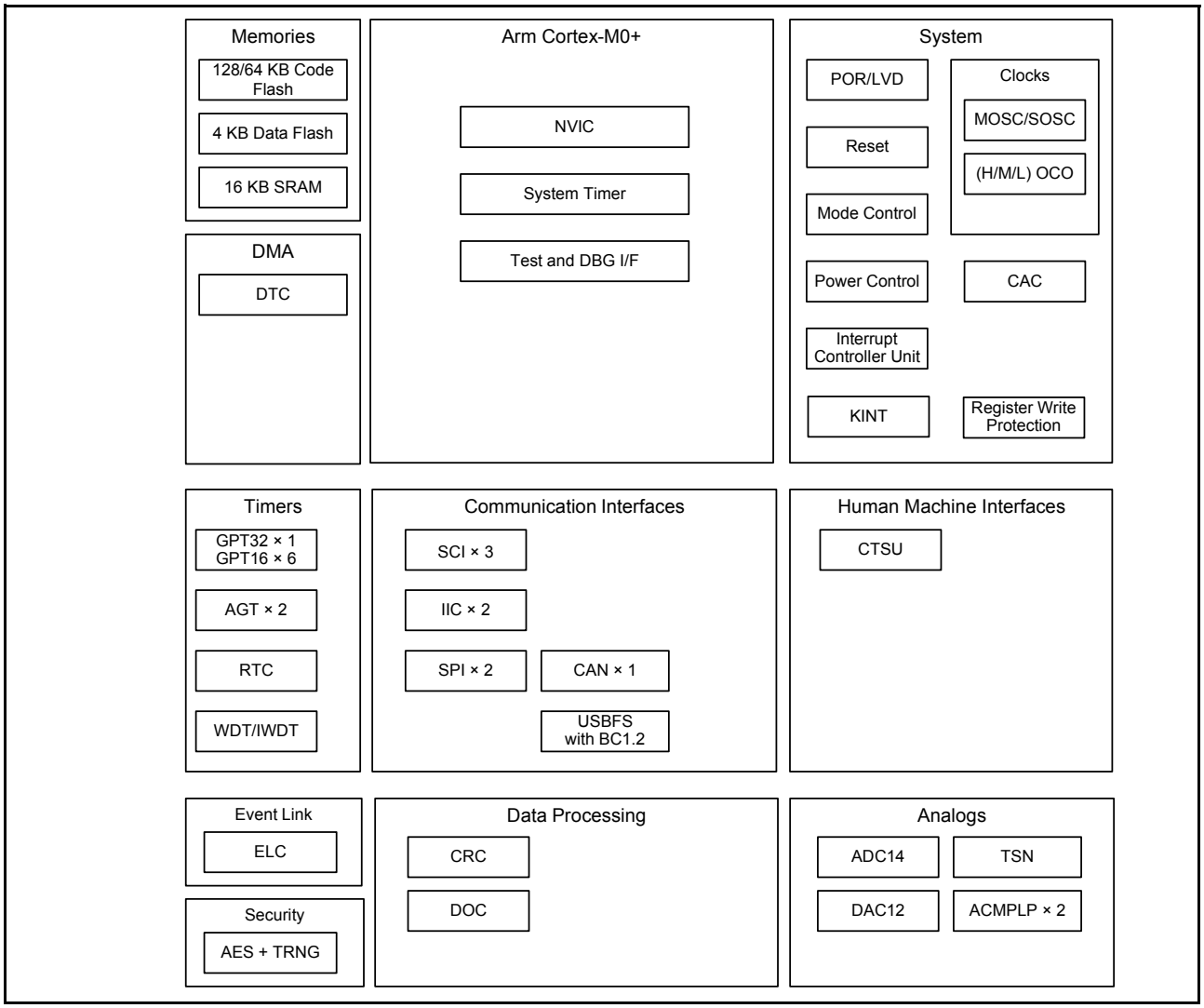


Figure 1.1 Block diagram

1.3 Part Numbering

Figure 1.2 shows how to read the product part number, memory capacity, and package types. Table 1.12 shows a list of products.

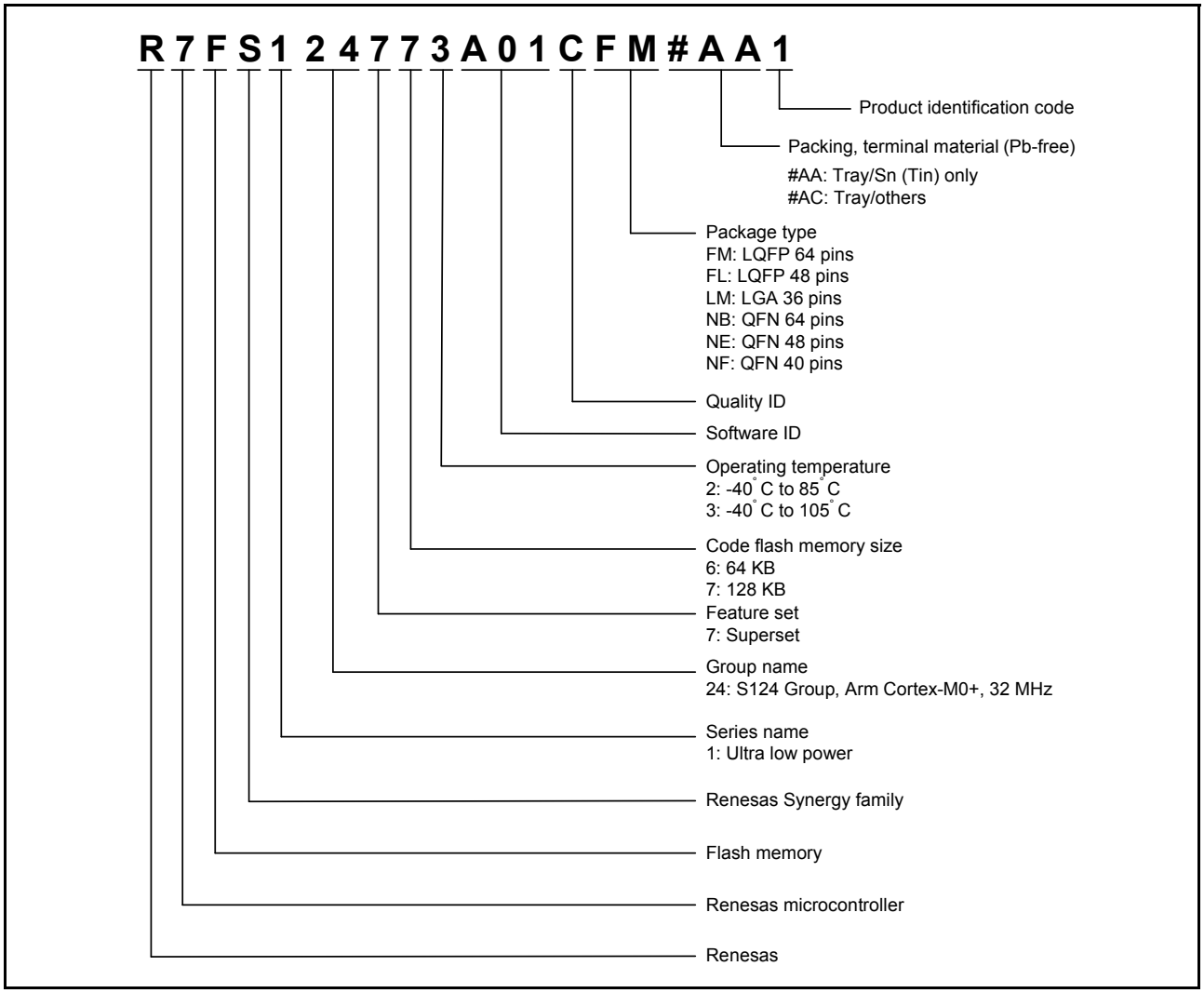


Figure 1.2 Part numbering scheme

Table 1.12 Product list

Product part number	Orderable part number	Package code	Code flash	Data flash	SRAM	Operating temperature
R7FS124773A01CFM	R7FS124773A01CFM#AA1	PLQP0064KB-C	128 KB	4 KB	16 KB	–40 to +105°C
R7FS124773A01CNB	R7FS124773A01CNB#AC1	PWQN0064LA-A				–40 to +105°C
R7FS124773A01CFL	R7FS124773A01CFL#AA1	PLQP0048KB-B				–40 to +105°C
R7FS124773A01CNE	R7FS124773A01CNE#AC1	PWQN0048KB-A				–40 to +105°C
R7FS124773A01CNF	R7FS124773A01CNF#AC1	PWQN0040KC-A				–40 to +105°C
R7FS124772A01CLM	R7FS124772A01CLM#AC1	PWLG0036KA-A				–40 to +85°C
R7FS124763A01CFM	R7FS124763A01CFM#AA1	PLQP0064KB-C	64 KB			–40 to +105°C
R7FS124763A01CFL	R7FS124763A01CFL#AA1	PLQP0048KB-B				–40 to +105°C
R7FS124762A01CLM	R7FS124762A01CLM#AC1	PWLG0036KA-A				–40 to +85°C

Note: Earlier products with orderable part number suffix AA0 and AC0 have a restriction in AES functions. If AES functions are required for your application, refer to the products with orderable part number suffix AA1 or AC1. For details on the differences of AES functions between AA0/AC0 and AA1/AC1 products, see *Technical Update (TN-SY*-A024A/E)*. Contact your Renesas sales representative for additional information.

Pin number					Power, System, Clock, Debug, CAC	I/O ports	Timers				Communication Interfaces				Analogs		HMI	
LQFP64, QFN64	LQFP48	QFN48	QFN40	LGA36			AGT	GPT_OPS, POEG	GPT	RTC	USBFS,CAN	SCI	IIC	SPI	ADC14	DAC12, ACMPLP	CTSU	Interrupt
35	27	27	23	D5		P110		GTOVLO_A	GTIOC1B_A		CRX0_A	CTS0_RTS0_C/SS0_C/RXD9_B/MISO9_B/SCL9_B		MISOB_B		VCOUT	TS11	IRQ3
36	28	28	24	D6		P111			GTIOC3A_A			SCK0_C/SCK9_B		RSPCKB_B			TS12	IRQ4
37	29	29	25	C6		P112			GTIOC3B_A			TXD0_C/MOSI0_C/SDA0_C					TSCAP_C	
38	-	-	-	-		P113												
39	30	30	-	-	VCC													
40	31	31	-	-	VSS													
41	-	-	-	-		P107			GTIOC0A_B									KR07
42	-	-	-	-		P106			GTIOC0B_B					SSLA3_A				KR06
43	-	-	-	-		P105		GTETRGA_C						SSLA2_A				KR05/IRQ0
44	32	32	26	-		P104		GTETRGB_B				RXD0_C/MISO0_C/SCL0_C		SSLA1_A			TS13	KR04/IRQ1
45	33	33	27	C3		P103		GTOWUP_A	GTIOC2A_A		CTX0_C	CTS0_RTS0_A/SS0_A		SSLA0_A	AN019	CMPREF1	TS14	KR03
46	34	34	28	C4		P102	AGTO0	GTOWLO_A	GTIOC2B_A		CRX0_C	SCK0_A		RSPCKA_A	AN020/ADTRG0_A	CMPIN1	TS15	KR02
47	35	35	29	C5		P101	AGTEE0	GTETRGB_A	GTIOC5A_A			TXD0_A/MOSI0_A/SDA0_A/CTS1_RTS1_A/SS1_A	SDA1_B	MOSIA_A	AN021	CMPREF0	TS16	KR01/IRQ1
48	36	36	30	B6		P100	AGTIO0_A	GTETRGA_A	GTIOC5B_A			RXD0_A/MISO0_A/SCL0_A/SCK1_A	SCL1_B	MISOA_A	AN022	CMPIN0	TS26	KR00/IRQ2
49	37	37	-	-		P500	AGTOA0	GTIU_B	GTIOC2A_B						AN016		TS27	
50	-	-	-	-		P501	AGTOB0	GTIV_B	GTIOC2B_B						AN017			
51	-	-	-	-		P502		GTIW_B	GTIOC3B_B						AN018			
52	38	38	31	A6		P015									AN010		TS28	IRQ7
53	39	39	32	A5		P014									AN009	DA0		
54	40	40	33	B5		P013									AN008			
55	41	41	34	B4		P012									AN007			
56	42	42	35	A4	AVCC0													
57	43	43	36	A3	AVSS0													
58	44	44	37	B3	VREFL0	P011									AN006		TS31	
59	45	45	38	A2	VREFH0	P010									AN005		TS30	
60	-	-	-	-		P004									AN004		TS25	IRQ3
61	-	-	-	-		P003									AN003		TS24	
62	46	46	-	-		P002									AN002		TS23	IRQ2
63	47	47	39	-		P001									AN001		TS22	IRQ7
64	48	48	40	B2		P000									AN000		TS21	IRQ6

Note: Several pin names have the added suffix of _A, _B, _C, and _D. The suffix can be ignored when assigning functionality.

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

VCC*1 = AVCC0 = VCC_USB*2 = VCC_USB_LDO*2 = 1.6 to 5.5V, VREFH0 = 1.6 to AVCC0,

VSS = AVSS0 = VREFL0 = VSS_USB = 0 V, Ta = T_{opr}

Note 1. The typical condition is set to VCC = 3.3V.
Note 2. When USBFS is not used.

Figure 2.1 shows the timing conditions.

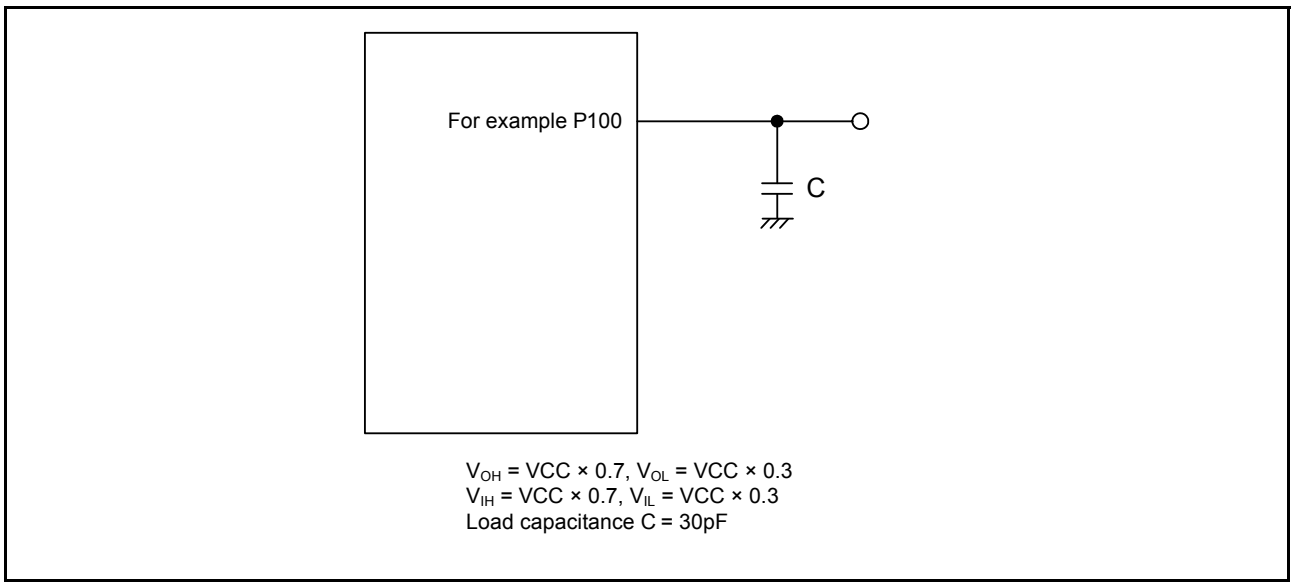


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation. However, make sure to adjust driving abilities of each pins to meet your conditions.

Each function pin used for the same function must select the same drive ability. If I/O drive ability of each function is mixed, the AC specification of the function is not guaranteed.

Note 2. t_{cac}: CAC count clock source cycle.

2.3.8 SCI Timing

Table 2.32 SCI timing (1)
Conditions: VCC = AVCC0 = 1.6 to 5.5 V

Parameter				Symbol	Min	Max	Unit*1	Test conditions
SCI	Input clock cycle	Asynchronous		t_{Scyc}	4	-	t_{Pcyc}	Figure 2.41
		Clock synchronous			6	-		
	Input clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Input clock rise time			t_{SCKr}	-	20	ns	
	Input clock fall time			t_{SCKf}	-	20	ns	
	Output clock cycle	Asynchronous		t_{Scyc}	6	-	t_{Pcyc}	
		Clock synchronous			4	-		
	Output clock pulse width			t_{SCKW}	0.4	0.6	t_{Scyc}	
	Output clock rise time		1.8V or above	t_{SCKr}	-	20	ns	
			1.6V or above		-	30		
	Output clock fall time		1.8V or above	t_{SCKf}	-	20	ns	
			1.6V or above		-	30		
	Transmit data delay (master)	Clock synchronous	1.8V or above	t_{TXD}	-	40	ns	Figure 2.42
			1.6V or above		-	45		
	Transmit data delay (slave)	Clock synchronous	2.7V or above		-	55	ns	
			2.4V or above		-	60		
			1.8V or above		-	100		
			1.6V or above		-	125		
	Receive data setup time (master)	Clock synchronous	2.7V or above	t_{RXS}	45	-	ns	
			2.4V or above		55	-		
			1.8V or above		90	-		
			1.6V or above		110	-		
	Receive data setup time (slave)	Clock synchronous	2.7V or above		40	-	ns	
			1.6V or above		45	-		
	Receive data hold time (master)	Clock synchronous		t_{RXH}	5	-	ns	
	Receive data hold time (slave)	Clock synchronous		t_{RXH}	40	-	ns	

Note 1. t_{Pcyc}: PCLKB cycle.

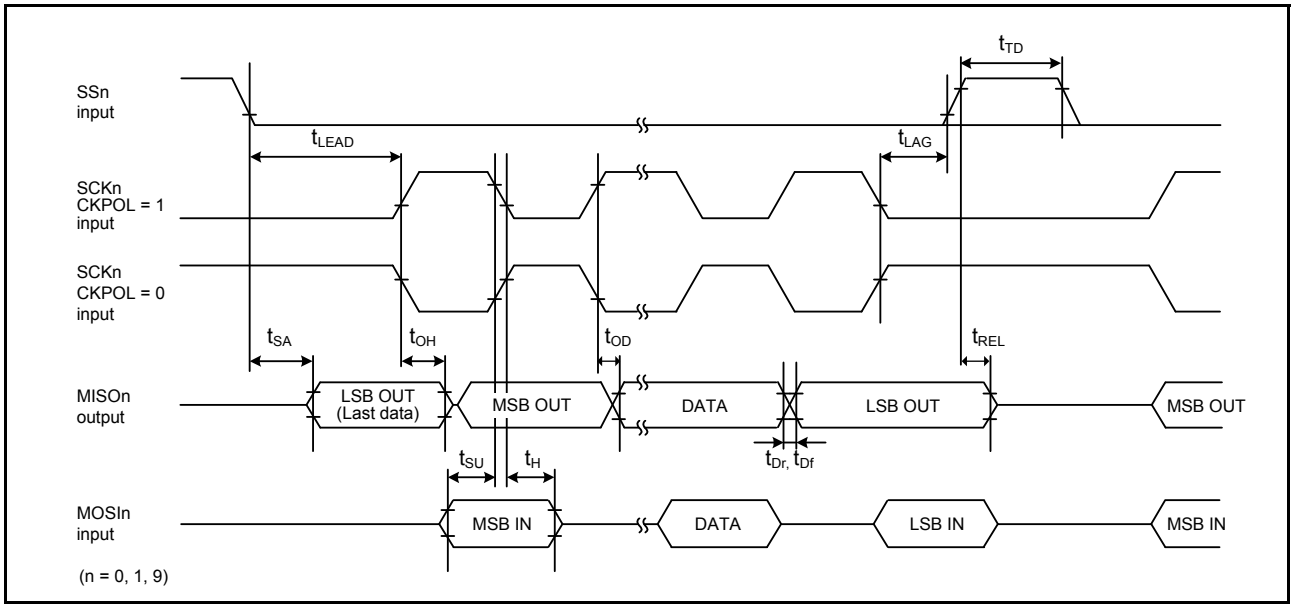


Figure 2.47 SCI simple SPI mode timing (slave, CKPH = 0)

Table 2.34 SCI timing (3)

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	Min	Max	Unit	Test conditions
Simple IIC (Standard mode)	SDA input rise time	t_{Sr}	-	1000	ns	Figure 2.48
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	4 × t_{IICcyc}	ns	
	Data input setup time	t_{SDAS}	250	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b*1	-	400	pF	
Simple IIC*2 (Fast mode)	SDA input rise time	t_{Sr}	-	300	ns	Figure 2.48
	SDA input fall time	t_{Sf}	-	300	ns	
	SDA input spike pulse removal time	t_{SP}	0	4 × t_{IICcyc}	ns	
	Data input setup time	t_{SDAS}	100	-	ns	
	Data input hold time	t_{SDAH}	0	-	ns	
	SCL, SDA capacitive load	C_b*1	-	400	pF	

Note: t_{IICcyc}: Clock cycle selected by the SMR.CKS[1:0] bits.

Note 1. Cb indicates the total capacity of the bus line.

Note 2. Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register.

Table 2.35 SPI timing (2 of 2)

Conditions: Middle drive output is selected in the Port Drive Capability bit in the PmnPFS register.

Parameter				Symbol	Min	Max	Unit*1	Test conditions
SPI	Data output delay	Master	2.7V or above	t_{OD}	-	14	ns	Figure 2.50 to Figure 2.55 C = 30pF
			2.4V or above		-	20		
			1.8V or above		-	25		
			1.6V or above		-	30		
		Slave	2.7V or above		-	50		
			2.4V or above		-	60		
			1.8V or above		-	85		
			1.6V or above		-	110		
	Data output hold time	Master		t_{OH}	0	-	ns	
		Slave			0	-		
	Successive transmission delay	Master		t_{TD}	t_{SPcyc} + 2 × t_{Pcyc}	8 × t_{SPcyc} + 2 × t_{Pcyc}	ns	
		Slave			6 × t_{Pcyc}	-		
	MOSI and MISO rise and fall time	Output	2.7V or above	t_{Dr}, t_{Df}	-	10	ns	
			2.4V or above		-	15		
			1.8V or above		-	20		
			1.6V or above		-	30		
		Input			-	1	µs	
	SSL rise and fall time	Output	2.7V or above	t_{SSLr}, t_{SSLf}	-	10	ns	
			2.4V or above		-	15		
			1.8V or above		-	20		
			1.6V or above		-	30		
		Input			-	1	µs	
	Slave access time		2.4V or above	t_{SA}	-	2 × t_{Pcyc} +100	ns	Figure 2.54 and Figure 2.55 C = 30pF
			1.8V or above		-	2 × t_{Pcyc} +140		
			1.6V or above		-	2 × t_{Pcyc} +180		
	Slave output release time		2.4V or above	t_{REL}	-	2 × t_{Pcyc} +100	ns	
			1.8V or above		-	2 × t_{Pcyc} +140		
			1.6V or above		-	2 × t_{Pcyc} +180		

Note 1. t_{Pcyc}: PCLKB cycle.

Note 2. N is set as an integer from 1 to 8 by the SPCKD register.

Note 3. N is set as an integer from 1 to 8 by the SSLND register.

2.3.11 CLKOUT Timing

Table 2.37 CLKOUT timing

Parameter			Symbol	Min	Max	Unit*1	Test conditions
CLKOUT	CLKOUT pin output cycle*1	VCC = 2.7 V or above	t_{Ccyc}	62.5	-	ns	Figure 2.57
		VCC = 1.8 V or above		125	-		
		VCC = 1.6 V or above		250	-		
	CLKOUT pin high pulse width*2	VCC = 2.7 V or above	t_{CH}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin low pulse width*2	VCC = 2.7 V or above	t_{CL}	15	-	ns	
		VCC = 1.8 V or above		30	-		
		VCC = 1.6 V or above		150	-		
	CLKOUT pin output rise time	VCC = 2.7 V or above	t_{Cr}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		
	CLKOUT pin output fall time	VCC = 2.7 V or above	t_{Cf}	-	12	ns	
		VCC = 1.8 V or above		-	25		
		VCC = 1.6 V or above		-	50		

Note 1. When the EXTAL external clock input or an oscillator is used with division by 1 (the CKOCR.CKOSEL[2:0] bits are 011b and the CKOCR.CKODIV[2:0] bits are 000b) to output from CLKOUT, the above should be satisfied with an input duty cycle of 45 to 55%.

Note 2. When the MOCO is selected as the clock output source (the CKOCR.CKOSEL[2:0] bits are 001b), set the clock output division ratio selection to be divided by 2 (the CKOCR.CKODIV[2:0] bits are 001b).

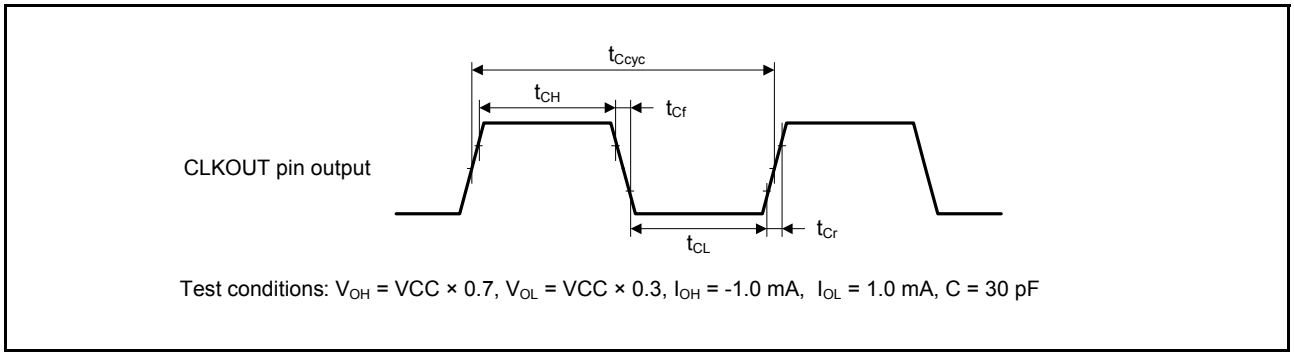


Figure 2.57 CLKOUT output timing

Table 2.42 A/D conversion characteristics (3) in high-speed A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 32 MHz)	Permissible signal source impedance Max. = 1.3 kΩ	1.59	-	-	µs	High-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 0Dh
		2.44	-	-	µs	Normal-precision channel ADCSR.ADHSC = 0 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

Table 2.43 A/D conversion characteristics (4) in low-power A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 2.7 to 5.5 V, VREFH0 = 2.7 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	24	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	2.5*3	kΩ	High-precision channel
		-	-	6.7*3	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-
Conversion time*1 (Operation at PCLKD = 24 MHz)	Permissible signal source impedance Max. = 1.1 kΩ	2.25	-	-	µs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		3.38	-	-	µs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±0.5	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-

Table 2.44 A/D conversion characteristics (5) in low-power A/D conversion mode (2 of 2)
Conditions: VCC = AVCC0 = 2.4 to 5.5 V, VREFH0 = 2.4 to 5.5 V, VSS = AVSS0 = VREFL0 = 0V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Full-scale error		-	±0.75	±4.5	LSB	High-precision channel
				±6.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±1.25	±5.0	LSB	High-precision channel
				±8.0	LSB	Other than above
DNL differential nonlinearity error		-	±1.0	-	LSB	-
INL integral nonlinearity error		-	±1.0	±3.0	LSB	-
14-bit mode						
Resolution		-	-	14	Bit	-
Conversion time*1 (Operation at PCLKD = 16 MHz)	Permissible signal source impedance Max. = 2.2 kΩ	3.75	-	-	µs	High-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 0Dh
		5.44	-	-	µs	Normal-precision channel ADCSR.ADHSC = 1 ADSSTRn.SST[7:0] = 28h
Offset error		-	±2.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Full-scale error		-	±3.0	±18	LSB	High-precision channel
				±24.0	LSB	Other than above
Quantization error		-	±0.5	-	LSB	-
Absolute accuracy		-	±5.0	±20	LSB	High-precision channel
				±32.0	LSB	Other than above
DNL differential nonlinearity error		-	±4.0	-	LSB	-
INL integral nonlinearity error		-	±4.0	±12.0	LSB	-

Note: The characteristics apply when no pin functions other than 14-bit A/D converter input are used. Absolute accuracy does not include quantization errors. Offset error, full-scale error, DNL differential nonlinearity error, and INL integral nonlinearity error do not include quantization errors.
Note 1. The conversion time is the sum of the sampling time and the comparison time. The number of sampling states is indicated for the test conditions.
Note 2. Except for I/O input capacitance (Cin), see section 2.2.4, I/O VOH, VOL, and Other Characteristics.
Note 3. Reference data.

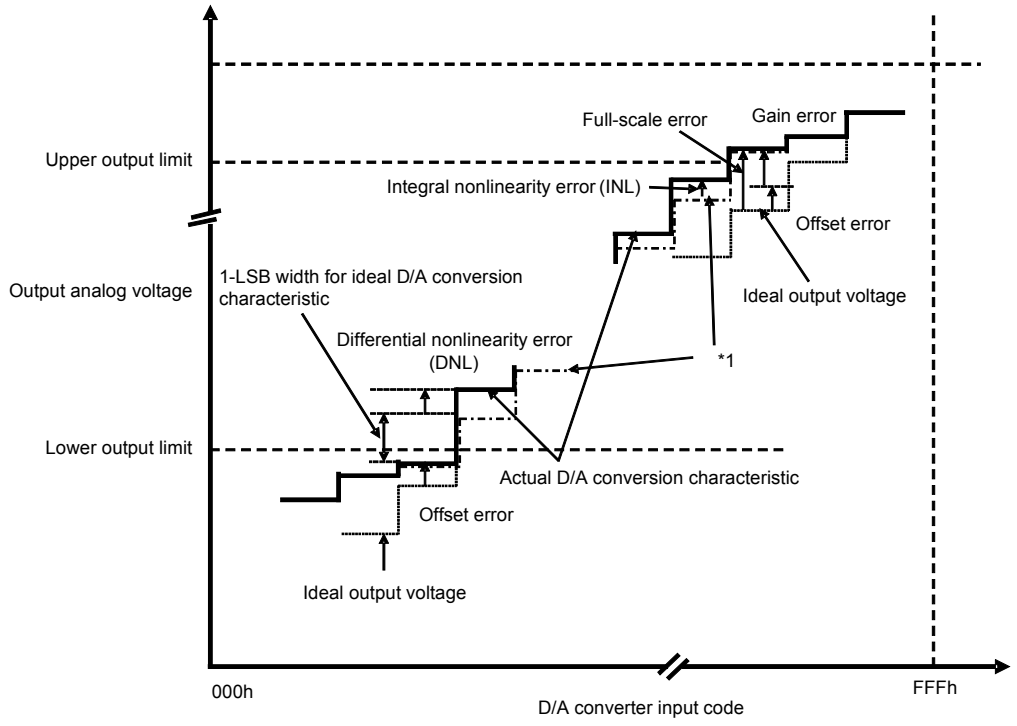
Table 2.45 A/D conversion characteristics (6) in low-power A/D conversion mode (1 of 2)
Conditions: VCC = AVCC0 = 1.8 to 5.5 V (AVCC0 = VCC when VCC < 2.0 V), VREFH0 = 1.8 to 5.5 V, VSS = AVSS0 = VREFL0 = 0 V
Reference voltage range applied to the VREFH0 and VREFL0.

Parameter		Min	Typ	Max	Unit	Test Conditions
Frequency		1	-	8	MHz	-
Analog input capacitance*2	Cs	-	-	8*3	pF	High-precision channel
		-	-	9*3	pF	Normal-precision channel
Analog input resistance	Rs	-	-	3.8*3	kΩ	High-precision channel
		-	-	8.2*3	kΩ	Normal-precision channel
Analog input voltage range	Ain	0	-	VREFH0	V	-
12-bit mode						
Resolution		-	-	12	Bit	-

2.6 DAC12 Characteristics

Table 2.49 D/A conversion characteristics
Conditions: VCC = AVCC0 = 1.8 to 5.5 V
Reference voltage = AVCC0 or AVSS0 selected

Parameter	Min	Typ	Max	Unit	Test conditions
Resolution	-	-	12	bit	-
Resistive load	30	-	-	kΩ	-
Capacitive load	-	-	50	pF	-
Output voltage range	0.35	-	AVCC0 – 0.47	V	-
DNL differential nonlinearity error	-	±0.5	±2.0	LSB	-
INL integral nonlinearity error	-	±2.0	±8.0	LSB	-
Offset error	-	-	±30	mV	-
Full-scale error	-	-	±30	mV	-
Output impedance	-	5	-	Ω	-
Conversion time	-	-	30	µs	-



Note 1. Ideal D/A conversion output voltage that is adjusted so that offset and full scale errors are zeroed

Figure 2.64 Illustration of D/A converter characteristic terms

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal output voltage based on the ideal conversion characteristic when the measured offset and full-scale errors are zeroed, and the actual output voltage.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between 1-LSB voltage width based on the ideal D/A conversion characteristics and the width of the actual output voltage.

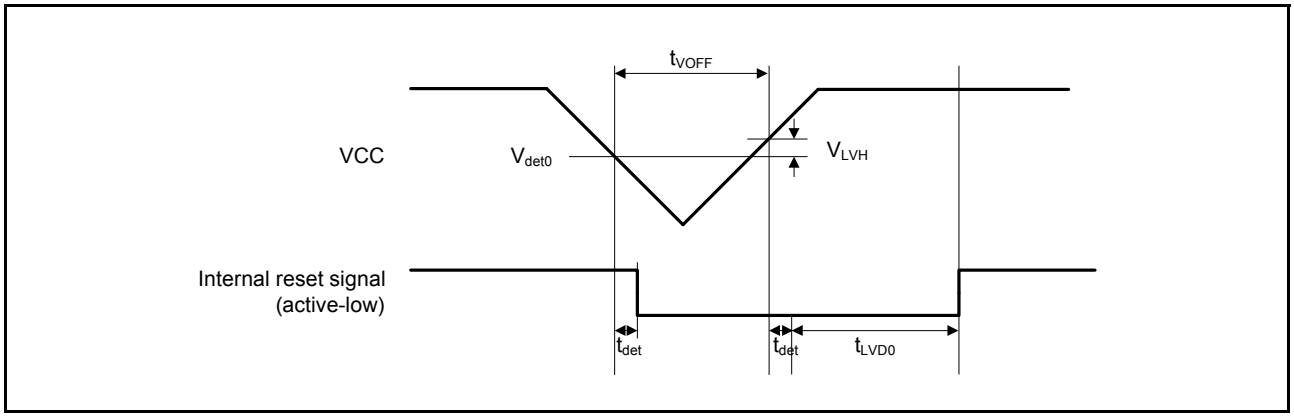


Figure 2.68 Voltage detection circuit timing (V_{det0})

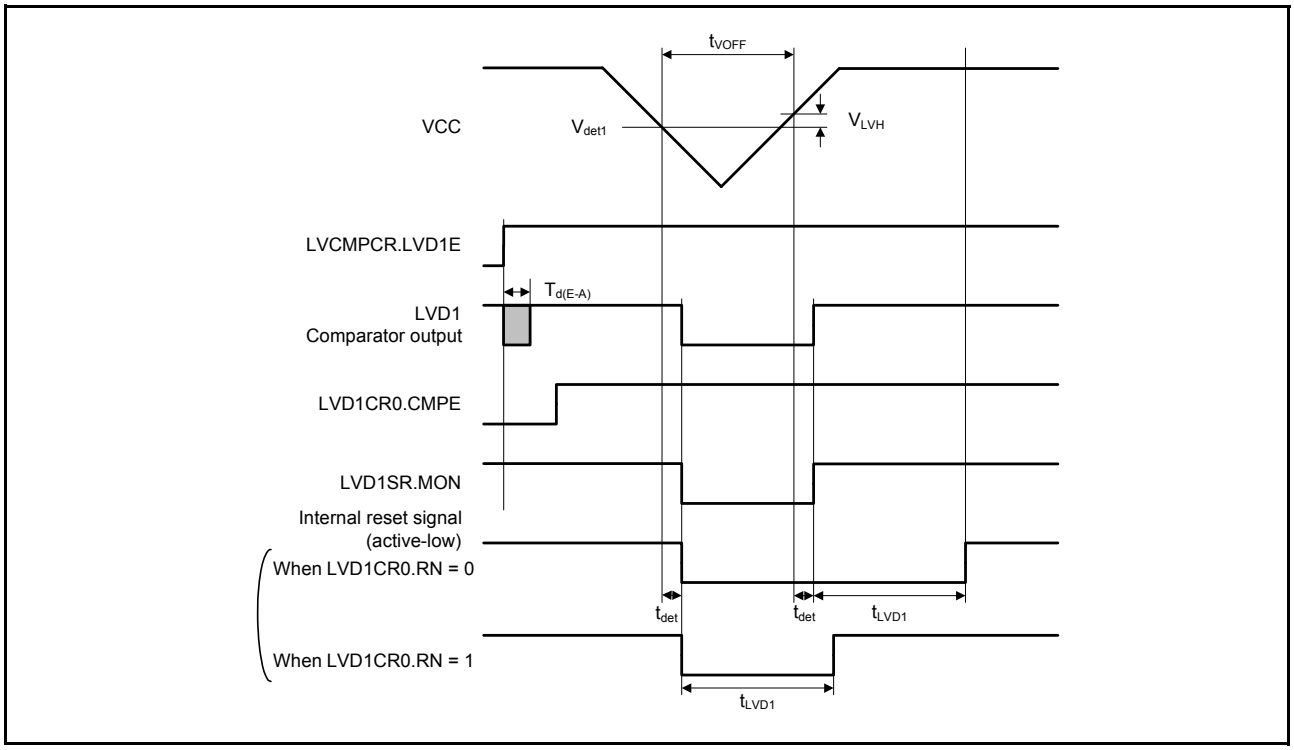


Figure 2.69 Voltage detection circuit timing (V_{det1})

2.11 Comparator Characteristics

Table 2.55 ACMPLP characteristics
Conditions: VCC = AVCC0 = 1.8 to 5.5 V, VSS = AVSS0 = 0 V

Parameter		Symbol	Min	Typ	Max	Unit	Test conditions
Reference voltage range		V_{REF}	0	-	VCC –1.4	V	-
Input voltage range		V_I	0	-	VCC	V	-
Internal reference voltage		-	1.36	1.44	1.50	V	-
Output delay	High-speed mode	T_d	-	-	1.2	µs	VCC = 3.0 Slew rate of input signal > 50 mV/µs
	Low-speed mode		-	-	5	µs	
	Window mode		-	-	2	µs	
Offset voltage	High-speed mode	-	-	-	50	mV	-
	Low-speed mode	-	-	-	40	mV	-
	Window mode	-	-	-	60	mV	-
Internal reference voltage for window mode		V_{RFH}	-	0.76 × VCC	-	V	-
		V_{RFL}	-	0.24 × VCC	-	V	-
Operation stabilization wait time		T_{cmp}	100	-	-	µs	-

2.12 Flash Memory Characteristics

2.12.1 Code Flash Memory Characteristics

Table 2.56 Code flash characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N_{PEC}	1000	-	-	Times	-
Data hold time	After 1000 times N_{PEC}	t_{DRP}	20*2, *3	-	-	Year	T_a = +85°C

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times (n = 1,000), erasing can be performed n times for each block. For instance, when 4-byte programming is performed 256 times for different addresses in 1-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)

Note 2. Characteristic when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. This result is obtained from reliability testing.

Table 2.57 Code flash characteristics (2)

High-speed operating mode

Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	ICLK = 1 MHz			ICLK = 32 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	4-byte	t_{P4}	-	116	998	-	54	506	µs
Erasure time	1-KB	t_{E1K}	-	9.03	287	-	5.67	222	ms
Blank check time	4-byte	t_{BC4}	-	-	56.8	-	-	16.6	µs
	1-KB	t_{BC1K}	-	-	1899	-	-	140	µs
Erase suspended time		t_{SED}	-	-	22.5	-	-	10.7	µs
Startup area switching setting time		t_{SAS}	-	21.9	585	-	12.1	447	ms
Access window time		t_{AWS}	-	21.9	585	-	12.1	447	ms
OCD/serial programmer ID setting time		t_{OSIS}	-	21.9	585	-	12.1	447	ms
Flash memory mode transition wait time 1		t_{DIS}	2	-	-	2	-	-	µs
Flash memory mode transition wait time 2		t_{MS}	5	-	-	5	-	-	µs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Table 2.58 Code flash characteristics (3)

Middle-speed operating mode

Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter		Symbol	ICLK = 1 MHz			ICLK = 8 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	4-byte	t_{P4}	-	157	1411	-	101	966	µs
Erasure time	1-KB	t_{E1K}	-	9.10	289	-	6.10	228	ms
Blank check time	2-byte	t_{BC4}	-	-	87.7	-	-	52.5	µs
	1-KB	t_{BC1K}	-	-	1930	-	-	414	µs
Erase suspended time		t_{SED}	-	-	32.7	-	-	21.6	µs
Startup area switching setting time		t_{SAS}	-	22.8	592	-	14.2	465	ms
Access window time		t_{AWS}	-	22.8	592	-	14.2	465	ms
OCD/serial programmer ID setting time		t_{OSIS}	-	22.8	592	-	14.2	465	ms
Flash memory mode transition wait time 1		t_{DIS}	2	-	-	2	-	-	µs
Flash memory mode transition wait time 2		t_{MS}	720	-	-	720	-	-	ns

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.

Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.

Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

2.12.2 Data Flash Memory Characteristics

Table 2.59 Data flash characteristics (1)

Parameter		Symbol	Min	Typ	Max	Unit	Conditions
Reprogramming/erasure cycle*1		N_{DPEC}	100000	1000000	-	Times	-
Data hold time	After 10000 times of N_{DPEC}	t_{DDRP}	20*2, *3	-	-	Year	Ta = +85°C
	After 100000 times of N_{DPEC}		5*2, *3	-	-	Year	
	After 1000000 times of N_{DPEC}		-	1*2, *3	-	Year	Ta = +25°C

Note 1. The reprogram/erase cycle is the number of erasure for each block. When the reprogram/erase cycle is n times (n = 100,000), erasing can be performed n times for each block. For instance, when 1-byte programming is performed 1,000 times for different addresses in 1-byte blocks, and then the entire block is erased, the reprogram/erase cycle is counted as 1. However, programming the same address for several times as one erasure is not enabled. (overwriting is prohibited.)

Note 2. Characteristics when using the flash memory programmer and the self-programming library provided by Renesas Electronics.

Note 3. These results are obtained from reliability testing.

Table 2.60 Data flash characteristics (2)
High-speed operating mode
Conditions: VCC = AVCC0 = 2.7 to 5.5 V

Parameter		Symbol	ICLK = 4 MHz			ICLK = 32 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	1-byte	t_{DP1}	-	52.4	463	-	42.1	387	µs
Erasure time	1-KB	t_{DE1K}	-	8.98	286	-	6.42	237	ms
Blank check time	1-byte	t_{DBC1}	-	-	24.3	-	-	16.6	µs
	1-KB	t_{DBC1K}	-	-	1872	-	-	512	µs
Suspended time during erasing		t_{DSED}	-	-	13.0	-	-	10.7	µs
Data flash STOP recovery time		t_{DSTOP}	5	-	-	5	-	-	µs

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

Table 2.61 Data flash characteristics (3)
Middle-speed operating mode
Conditions: VCC = AVCC0 = 1.8 to 5.5 V, Ta = -40 to +85°C

Parameter		Symbol	ICLK = 4 MHz			ICLK = 8 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Programming time	1-byte	t_{DP1}	-	94.7	886	-	89.3	849	µs
Erasure time	1-KB	t_{DE1K}	-	9.59	299	-	8.29	273	ms
Blank check time	1-byte	t_{DBC1}	-	-	56.2	-	-	52.5	µs
	1-KB	t_{DBC1K}	-	-	2.17	-	-	1.51	ms
Suspended time during erasing		t_{DSED}	-	-	23.0	-	-	21.7	µs
Data flash STOP recovery time		t_{DSTOP}	720	-	-	720	-	-	ns

Note 1. Does not include the time until each operation of the flash memory is started after instructions are executed by the software.
Note 2. The lower-limit frequency of ICLK is 1 MHz during programming or erasing the flash memory. When using ICLK at below 4 MHz, the frequency can be set to 1 MHz, 2 MHz, or 3 MHz. A non-integer frequency such as 1.5 MHz cannot be set.
Note 3. The frequency accuracy of ICLK must be ±3.5% while programming or erasing the flash memory. Confirm the frequency accuracy of the clock source.

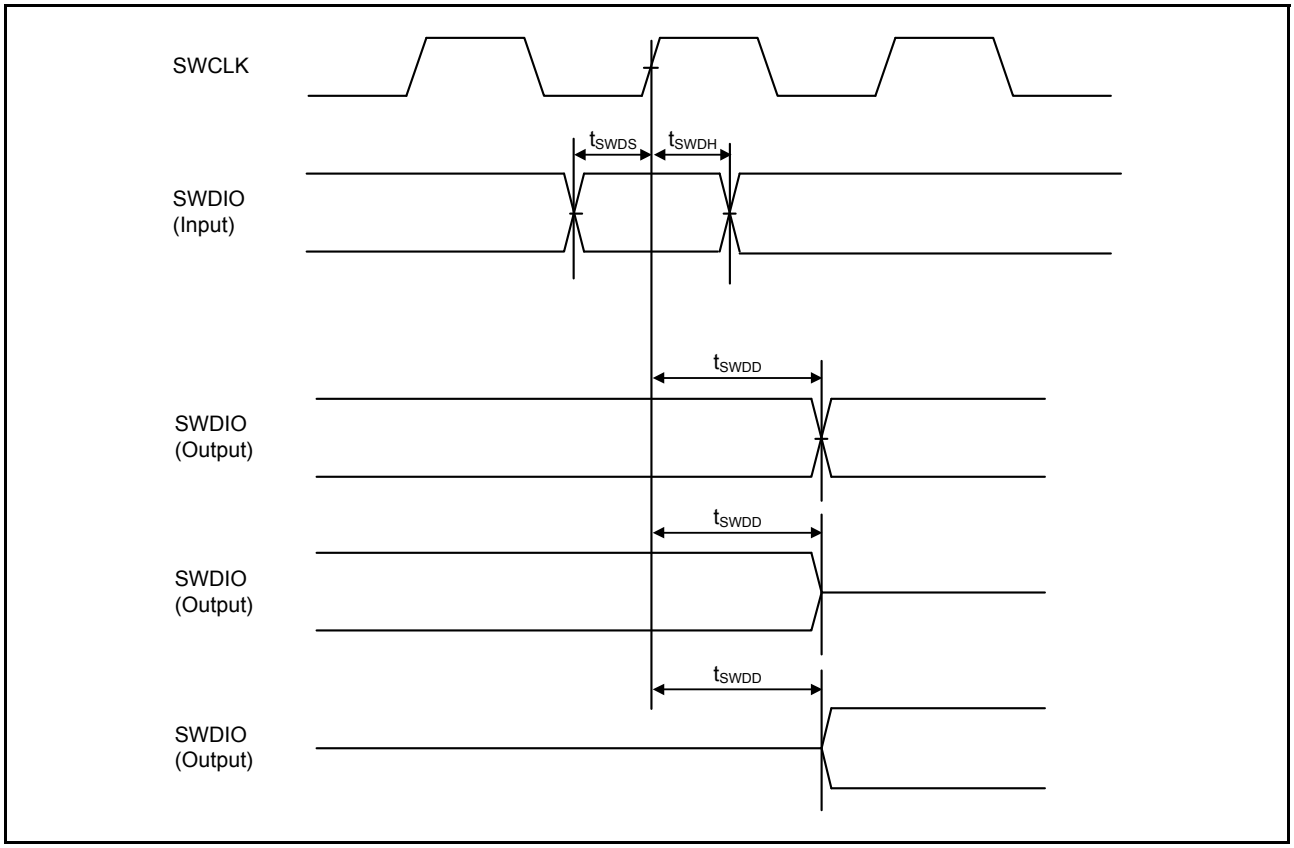


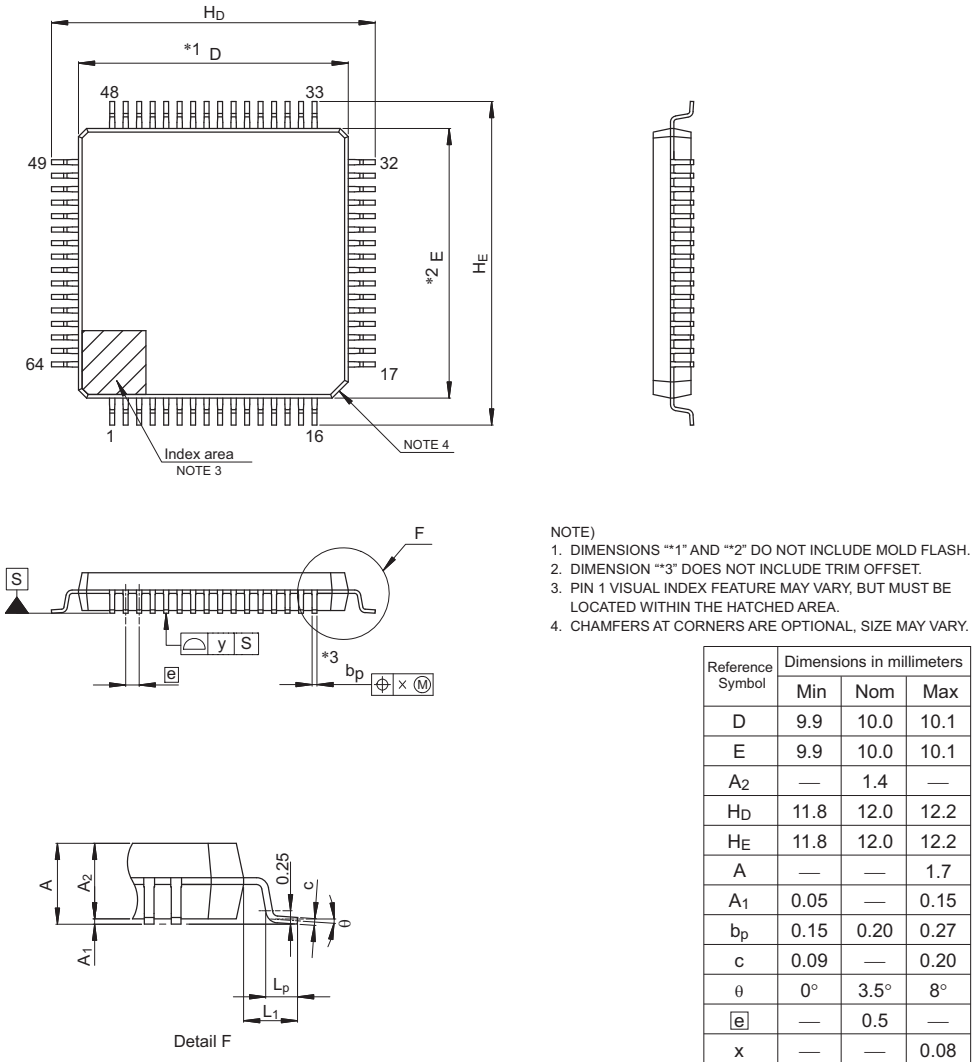
Figure 2.72 SWD input output timing

Appendix 1. Package Dimensions

Information on the latest version of the package dimensions or mountings is displayed in “Packages” on the Renesas Electronics Corporation website.

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP64-10x10-0.50	PLQP0064KB-C	—	0.3

Unit: mm

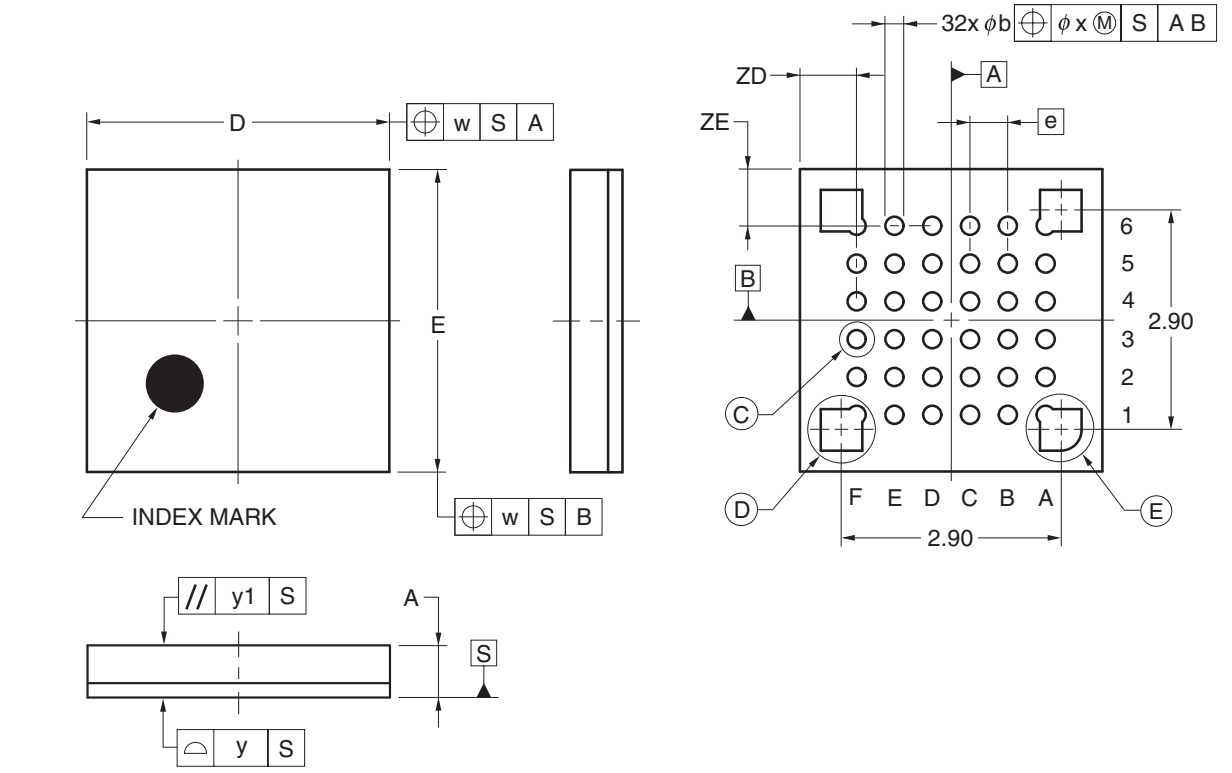


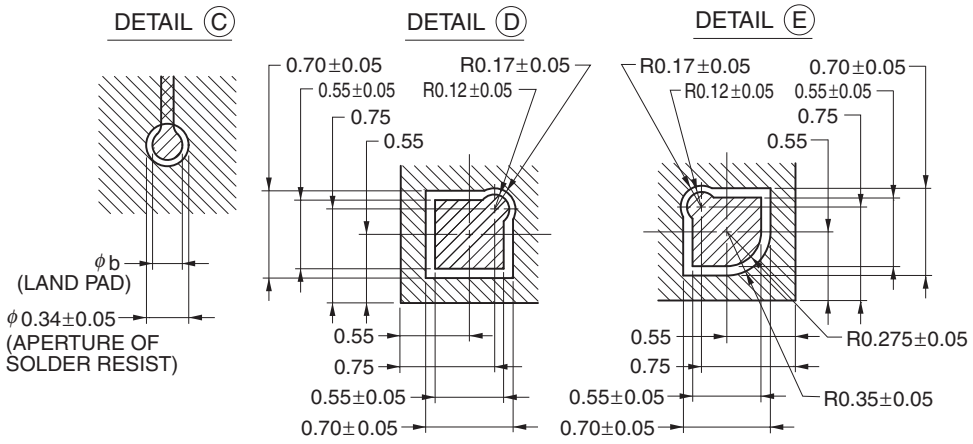
NOTE)
1. DIMENSIONS “*1” AND “*2” DO NOT INCLUDE MOLD FLASH.
2. DIMENSION “*3” DOES NOT INCLUDE TRIM OFFSET.
3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	—	0.15
b_p	0.15	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
L_p	0.45	0.6	0.75
L_1	—	1.0	—

Figure 1.1 LQFP 64-pin

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023





(UNIT:mm)

ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

Figure 1.3 LGA 36-pin

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(Rev.4.0-1 November 2017)

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